Supporting Information for

Enhanced performance of perovskite solar cells via bilateral electron-donating passivator as a molecule bridge

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Figures S1~S15

Tables S1~S3

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Figure S1. (a) The chemical structure of HAL. (b) The optimizing of geometries of HAL. The grey, white, green, and reddish brown atoms respectively represent the C, H, O, and N atoms.



Figure S2. Electrostatic potential (ESP) map of HAL molecules.



Figure S3. The XPS full spectra of the SnO_2 films without or with HAL modification.



Figure S4. Transmittance spectra of the pristine SnO_2 film, HAL-modified SnO_2 film, and ITO substrate.



Figure S5. UV-vis absorption spectra of the SnO_2 films without or with HAL modification.



Figure S6. Optical band gap energy (E_g) of the (a) pristine SnO₂ and (b) HAL-modified SnO₂ films.



Figure S7. The Tafel curves of devices with a structure of ITO/SnO_2 (without and with HAL)/Au.



Figure S8. Top-view SEM images of the (a) pristine SnO_2 and (b) HAL-modified SnO_2 films.



Figure S9. The AFM images of the (a) pristine SnO_2 and (b) HAL-modified SnO_2 films.



Figure S10. The contact angle measurements of the DMF/DMSO mixture solution on the (a)

pristine SnO_2 and (b) HAL-modified SnO_2 substrates.



Figure S11. The AFM images of perovskite films on the (a) pristine SnO_2 and (b) HALmodified SnO_2 films.



Figure S12. Optical band gap energy (E_g) of perovskite films on the (a) pristine SnO₂ and (b)

HAL-modified SnO₂ films.



Figure S13. Logarithm of absorption coefficient (α) versus photon energy and the Urbach energy calculated in the perovskite based on the (a) pristine SnO₂ and (b) HAL-modified SnO₂ films.



Figure S14. *J-V* curves of the pristine device and the devices modified with different concentrations of HAL solutions.



Figure S15. EQE spectrum and integrated current density of the HAL-modified device. The integrated current density is 24.40 mA cm^{-2} .



Figure S16. (a) V_{OC} , (b) J_{SC} , and (c) FF statistical diagrams of pristine and HAL-modified devices.

Tables S1-S3

Samples	E _{cutoff} (eV)	W _F (eV)	E _{onset} (eV)	E _{VBM} (eV)	E _{CBM} (eV)	$E_{g}(eV)$
Pristine	16.76	4.46	3.73	-8.19	-4.28	3.91
HAL-modified	16.68	4.54	3.76	-8.30	-4.39	3.91

Table S1 Energy levels of pristine SnO_2 film and HAL-modified SnO_2 film.

Table S2 TRPL parameters of perovskite on SnO_2 films without or wih HAL modification

from	Figure	3d.

Samples	$ au_{avg}$ (ns)	τ_l (ns)	$ au_2$ (ns)	A ₁ (%)	$A_{2}(\%)$
Pristine	96.56	35.93	113.41	21.74	78.26
HAL-modified	64.36	22.39	78.58	25.30	74.70

Table S3. Electrical impedance of the PSCs without or wih HAL modification.

Samples	$R_{s}\left(\Omega ight)$	$R_{ct}\left(\Omega ight)$	$R_{rec}\left(\Omega ight)$
Pristine	11.55	54.09	28.32
HAL-modified	10.84	24.45	90.07

Table S4 Photovoltaic data of PSCs based on SnO_2 films without or wih HAL modification.

Samples	$V_{OC}\left(\mathbf{V}\right)$	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
Pristine	1.110	24.41	78.61	21.30
0.5 mg mL^{-1}	1.148	24.66	81.19	22.99
1.0 mg mL^{-1}	1.155	24.82	82.27	23.58
1.5 mg mL^{-1}	1.142	24.75	80.90	22.87

Samples	$V_{OC}(\mathbf{V})$	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
Pristine	1.095±0.008	24.33±0.08	77.69±0.65	20.73±0.25
HAL-modified	1.147±0.007	24.74±0.07	81.45±0.47	23.11±0.22

Table S5 Photovoltaic data statistics of 20 PSCs based on SnO_2 films without or wih HALmodification.